

VHF/ UHF-Tuner-IC

Description

This tuner IC requires a power supply of 9 V and performs the function of three separate oscillators an mixers, SAWF-driver, L.O.-output and tri-state band switch. Additional to TV-tuner application this IC is usable for DAB (Digital Audio Broadcast) tuners.

Features

- 9 V supply voltage
- Frequency range from 48 to 860 MHz
- Band A: balanced high impedance mixer input and amplitude controlled oscillator
- Band B + C: balanced low impedance mixer input and symmetrical oscillator
- Balanced L. O.-outputs for prescalers or PLL
- SAW filter driver with low impedance output
- Voltage regulator for stable operating characteristics
- ESD protection on all pins except oscillator pins and RF-inputs

Benefits

• The integration of 3 bands and the small SSO28 package allows to design very small and economical 3-band tuners with high performance.

Block Diagram

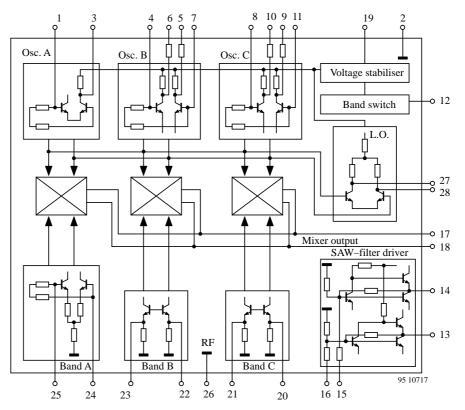


Figure 1. Block diagram

U2309B



Pin Description

1				
Osc A, base	1		28	L.O. out
GND (common)	2		27	L.O. out
Osc A, coll.	3		26	GND (RF)
Osc B, base	4		25	RF in, A
Osc B, coll.	5		24	RF in, A
Osc B, coll.	6		23	RF in, B
Osc B, base	7		22	RF in, B
Osc C, base	8		21	RF in, C
Osc C, coll.	9		20	RF in, C
Osc C, coll.	10		19	V_S
Osc C, base	11		18	Mix out
Band sw.	12		17	Mix out
SAWF, out	13		16	SAWF, inp.
SAWF, out	14		15	SAWF, inp.
	I	95 10886	J	

Pin	Symbol	Function
1	Osc A, base	Oscillator band A, base
2	GND	Ground, common
	(common)	
3	Osc A, coll.	Oscillator band A, collector
4, 7	Osc B, base	Oscillator band B, bases
5, 6	Osc B, coll.	Oscillator band B, collectors
8, 11	Osc C, base	Oscillator band C, bases
9, 10	Osc C, coll.	Oscillator band C, collectors
12	Band sw.	Tri-state band switch
13, 14	SAWF, out	SAW filter driver outputs
15, 16	SAWF, inp.	SAW filter driver inputs
17, 18	Mix out	Mixer outputs, open collec-
		tor
19	V_{S}	Supply voltage V _s
20, 21	RF in, C	RF inputs, band C
22, 23	RF in, B	RF inputs, band B
24, 25	RF in, A	RF inputs, band A
26	GND (RF)	Ground, RF part
27, 28	L.O. out	L.Ooutputs

Ordering Information

Extended Type Number	Package	Remarks
U2309B-FLG3	SO28	Taped and reeled
U2309B-FSG3	SSO28	Taped and reeled



Absolute Maximum Ratings

All voltages are referred to GND, Pin 2

Parameters		Symbol	Min.	Тур.	Max.	Unit
Supply voltage	Pin 19	V_{S}			10.5	V
RF inputs	Pin (20-25)				5.0	V
IF outputs	Pin 17-18				10.5	V
Tri-state switch voltage	Pin 12	ViTRI			10.5	V
Junction temperature		Tj			125	°C
Storage temperature		T _{stg}	-40		125	°C

Operating Range

All voltages are referred to GND, Pin 2

Parameters	Test Conditions / Pins	Symbol	Min	Тур	Max	Unit
Supply voltage	Pin 17-19	V_{S}	8.1	9	9.9	V
Ambient temperature		T _{amb}	-25		75	°C

Thermal Resistance

Parameters	Symbol	Тур	Unit
Junction ambient			
Package SO28 soldered to PCB	R_{thJA}	70	K/W
Package SSO28 soldered to PCB (see layout page 5)		128	

Electrical Characteristics

Test conditions (unless otherwise specified): $V_s = 9 \text{ V. } T_{amb} = 25 \text{ °C.}$ Reference point Pin 2

Parameters	Test Conditions / Pins	Symbol	Min	Тур	Max	Unit
Supply voltage	Pin 17-19	V_{S}	8.1	9.0	9.9	V
Supply current	Pin 17-19	I _S		42	50	mA
Band switch						
Voltage band A	Pin 1	2 VSWA	0	0	1.0	V
Voltage band B	Pin 1	2 VSWB	1.6	2.0	2.4	V
Voltage band C	Pin 1	2 VSWC	3.4	4.0	5.0	V
Switching current	VSW = 5 V Pin 1:	2 ISW			100	μΑ
L. Ooutput						
L. O. level each output	RL = 50 Ohm Pin 27, 28	PLO	-25		-17	dBm
SAW filter driver fi = 36 MHz						
Input impedance	Pin 15, 16	ZiSAW		450		Ohm
Output impedance	Pin 13, 14	ZoSAW		70		Ohm
Voltage gain	Pin 15, 16 \rightarrow 13, 14	GvSAW		17		dB

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Electrical Characteristics (continued)

Parameters	Test Conditions /	Pins	Symbol	Min	Тур	Max	Unit
Band A							
Input frequency range		Pin 24	fiA	48		170	MHz
Input impedance	Figure 3	Pin 24	S11A				
Gain (note 4)	Pin I	I/P to O/P	GA		28		dB
Noise figure DSB (note 2)		/P to O/P					
	fiA = 50 MHz		NF		11.5		dB
	fiA = 150 MHz		NF		12		dB
Input level for (note 3):	Each carrier						
IM3 (interm. of 3rd order	fiA = 71 MHz	Pin I/P	ViA		-23		dBm
IM2 (interm. of 2nd order)	fiA = 71 MHz	Pin I/P	ViA		-22		dBm
Band B (note 1)							
Input frequency range	I	Pin 22, 23	fiA	170		470	MHz
Input impedance	l	Pin 22, 23	S11B		see Fig. 3		
Gain (note 4)	Pin I	/P to O/P	GB		32		dB
Noise figure DSB (note 2)	Pin I/P to O/P						
	fiB = 200 MHz		NF		9.5		dB
	fiB = 450 MHz		NF		10		dB
Input level for (note 3):	Each carrier						
IM3 (interm. of 3rd order)	fiB = 300 MHz	Pin I/P	ViB		-28		dBm
Band C (note 1)							
Input frequency range	I	Pin 20, 21	fiC	470		860	MHz
Input impedance	Figure 3	Pin 20, 21	S11C				
Gain	Pin I	/P to O/P	GC		32		dB
Noise figure DSB (note 2)	Pin I/P to O/P						
	fiC = 500 MHZ		NF		10.5		dB
	fiC = 800 MHz		NF		11.5		dB
Input level for IM3	Each carrier		ViC		-28		dBm
(interm. of 3rd order, note 3)	fiC = 600 MHz	Pin I/P					

Notes

The RF inputs B and C are symmetrical driven by means of a hybrid for 180° phase shifting, consequently the source impedance is 100 Ω . All other impedance for RF tests is 50 Ω .

²⁾ The noise figure (NF) is the value for double-side-band measurement.

The intermodulation test (2-carrier-method) which is made on IF-centre is in reference to a signal-to-IM ratio of 60 dB.

Gain is the ratio of the voltage at the primary coil of L5 to the available voltage at the input.



Test and Principle Application Circuit

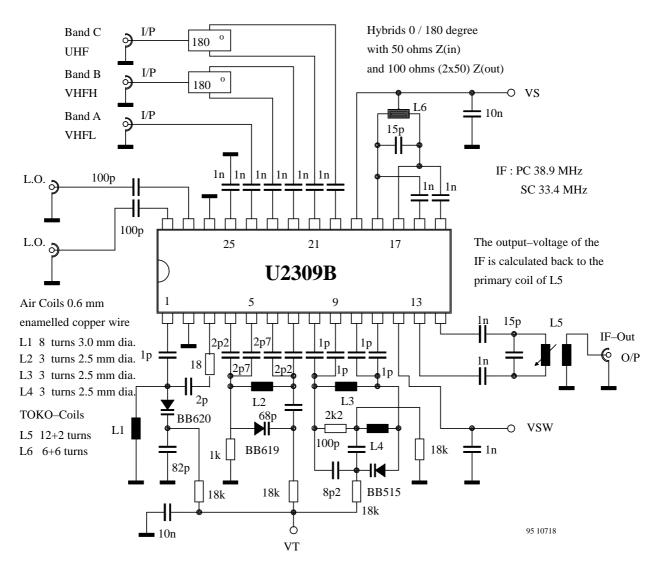


Figure 2. Test and principle application circuit

PCB for the $R_{thJA}\mbox{-}Measurement$

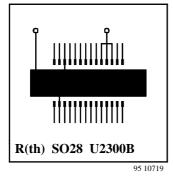


Figure 3. PCB for the R_{thJA}-measurement

Material: 35 μm one-sided Cu-coated epoxy PCB, $40 \text{ mm} \times 40 \text{ mm} \times 1.5 \text{ mm}$



Input Impedance Mixer Band A (S11A), B and C (S11B/C)

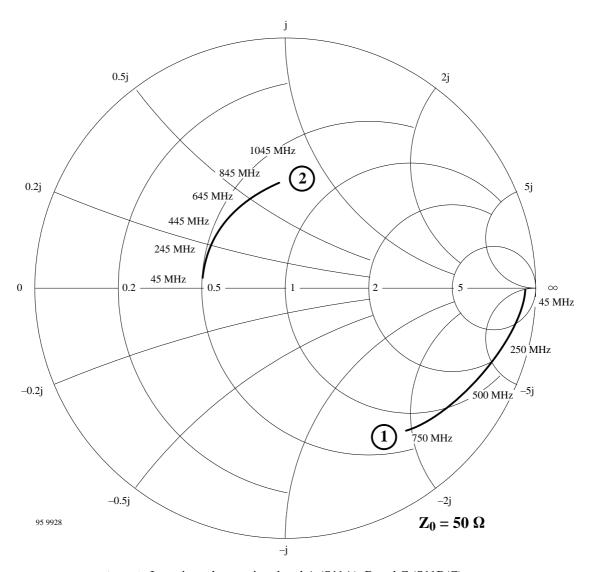


Figure 4. Input impedance mixer band A (S11A), B and C (S11B/C)

1) **VHF-low** Normalised to 50 Ω , measuring range 45 MHz to 750 MHz.

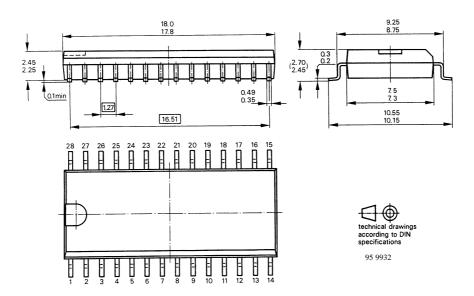
2) VHF-high and UHF

Normalised to 50 Ω , measuring range 45 MHz to 1045 MHz. Both inputs are driven symmetrical. The output impedance of hybrid is 100 Ω , the measured levels are then calculated in reference to 50 Ω .

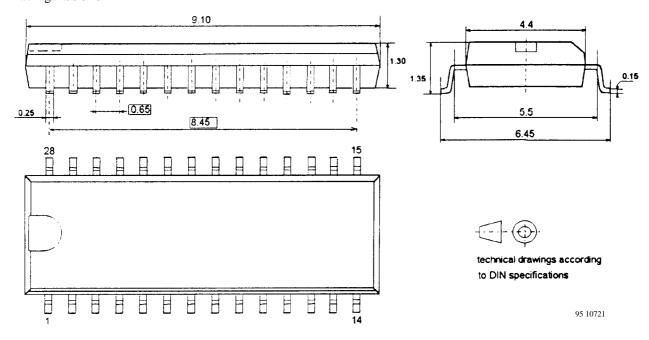


Dimensions in mm:

Package: SO28



Package: SSO28





Ozone Depleting Substances Policy Statement

It is the policy of TEMIC TELEFUNKEN microelectronic GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

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- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

TEMIC can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

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